Dual D Flip-Flop with Set and Reset

High-Performance Silicon-Gate CMOS

The 74HC74 is identical in pinout to the LS74. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device consists of two D flip-flops with individual Set, Reset, and Clock inputs. Information at a D-input is transferred to the corresponding Q output on the next positive going edge of the clock input. Both Q and \overline{Q} outputs are available from each flip-flop. The Set and Reset inputs are asynchronous.

Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the JEDEC Standard No. 7A Requirements
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 128 FETs or 32 Equivalent Gates
- Pb-Free Packages are Available



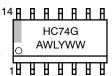
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MARKING DIAGRAMS



SOIC-14 D SUFFIX CASE 751A





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TSSOP-14 DT SUFFIX CASE 948G



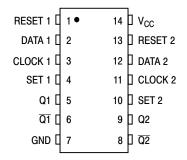
HC74 = Device Code A = Assembly Location

L, WL = Wafer Lot
Y = Year
W, WW = Work Week
G or = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

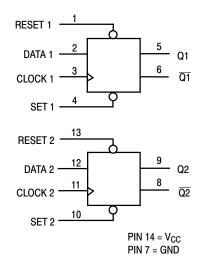
PIN ASSIGNMENT



FUNCTION TABLE

| | Inputs | | | | puts |
|-----|--------|---------------|------|-------|-------|
| Set | Reset | Clock | Data | Q | Q |
| L | Н | Х | Х | Н | L |
| Н | L | Χ | Χ | L | Н |
| L | L | Χ | X | H* | H* |
| Н | Н | | Н | Н | L |
| Н | Н | \mathcal{L} | L | L | Н |
| Н | Н | L | Χ | No Cl | nange |
| Н | Н | Н | Χ | No Cl | nange |
| Н | Н | ~ | Х | No Cl | nange |

LOGIC DIAGRAM



MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|------------------|---|--------------------------------|------|
| V _{CC} | DC Supply Voltage (Referenced to GND) | - 0.5 to + 7.0 | V |
| V _{in} | DC Input Voltage (Referenced to GND) | - 0.5 to V _{CC} + 0.5 | V |
| V _{out} | DC Output Voltage (Referenced to GND) | - 0.5 to V _{CC} + 0.5 | V |
| I _{in} | DC Input Current, per Pin | ±20 | mA |
| l _{out} | DC Output Current, per Pin | ±25 | mA |
| I _{CC} | DC Supply Current, V _{CC} and GND Pins | ±50 | mA |
| P _D | Power Dissipation in Still Air, SOIC Package† | 500 | mW |
| | TSSOP Package† | 450 | |
| T _{stg} | Storage Temperature | - 65 to + 150 | °C |
| TL | Lead Temperature, 1 mm from Case for 10 Seconds | | °C |
| | (SOIC or TSSOP Package) | 260 | |
| | | 300 | |

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and Vout should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

SOIC Package: $-~7~mW/^{\circ}C$ from 65° to $125^{\circ}C$ †Derating

TSSOP Package: - 6.1 mW/°C from 65° to 125°C
For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min | Max | Unit |
|------------------------------------|--|------|----------|------|
| V _{CC} | DC Supply Voltage (Referenced to GND) | 2.0 | 6.0 | V |
| V _{in} , V _{out} | DC Input Voltage, Output Voltage (Referenced to GND) | 0 | V_{CC} | V |
| T _A | Operating Temperature, All Package Types | - 55 | + 125 | °C |
| t _r , t _f | Input Rise and Fall Time V _{CC} = 2.0 V | 0 | 1000 | ns |
| | (Figures 1, 2, 3) V _{CC} = 3.0 V | 0 | 600 | |
| | $V_{CC} = 4.5 \text{ V}$ | 0 | 500 | |
| | $V_{CC} = 6.0 \text{ V}$ | 0 | 400 | |

^{*}Both outputs will remain high as long as Set and Reset are low, but the output states are unpredictable if Set and Reset go high simultaneously.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

| | | | | Gu | aranteed Li | mit | |
|-----------------|---|--|--|---|---|--|----------|
| Symbol | Parameter | Test Conditions | V _{CC} (V) | – 55 to 25°C | ≤ 85 °C | ≤ 125°C | Unit |
| V _{IH} | Minimum High-Level Input Voltage | $V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$ | 2.0 3.0 4.5 6.0 | 1.5 2.1 3.15 4.2 | 1.5 2.1 3.15 4.2 | 1.5 2.1 3.15 4.2 | V |
| V _{IL} | Maximum Low-Level Input Voltage | V_{out} = 0.1 V or V_{CC} – 0.1 V $ I_{out} \le 20 \mu A$ | 2.0 3.0 4.5 6.0 | 0.5 0.9 1.35 1.8 | 0.5 0.9 1.35 1.8 | 0.5 0.9 1.35 1.8 | V |
| V _{OH} | Minimum High-Level Output Voltage | $\begin{split} V_{in} &= V_{IH} \text{ or } V_{IL} \\ I_{out} &\leq 20 \mu\text{A} \end{split}$ $V_{in} &= V_{IH} \text{ or } V_{IL} I_{out} \leq 2.4 \text{ mA} \\ I_{out} &\leq 4.0 \text{ mA} \\ I_{out} &\leq 5.2 \text{ mA} \end{split}$ | 2.0 4.5 6.0 3.0 4.5 6.0 | 1.9 4.4 5.9 2.48 3.98 5.48 | 1.9 4.4 5.9 2.34 3.84 5.34 | 1.9 4.4 5.9 2.2 3.7 5.2 | V |
| V _{OL} | Maximum Low-Level Output Voltage | $\begin{split} V_{in} &= V_{IH} \text{ or } V_{IL} \\ I_{out} &\leq 20 \mu\text{A} \end{split}$ $V_{in} &= V_{IH} \text{ or } V_{IL} \begin{aligned} I_{out} &\leq 2.4 \text{ mA} \\ I_{out} &\leq 4.0 \text{ mA} \\ I_{out} &\leq 5.2 \text{ mA} \end{aligned}$ | 2.0 4.5 6.0 3.0 4.5 6.0 | 0.1 0.1 0.1 0.26 0.26 0.26 | 0.1 0.1 0.1 0.33 0.33 0.33 | 0.1 0.1 0.1 0.4 0.4 0.4 | V |
| I _{in} | Maximum Input Leakage Current | V _{in} = V _{CC} or GND | 6.0 | ±0.1 | ±1.0 | ±1.0 | μΑ |
| I _{CC} | Maximum Quiescent Supply Current (per Package) | $V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$ | 6.0 | 2.0 | 20 | 80 | μΑ |

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_{r} = t_{f} = 6.0 ns)

| | | | Gu | aranteed Li | mit | |
|--|--|--------------------------|-----------------------|-----------------------|------------------------|------|
| Symbol | Parameter | V _{CC} (V) | – 55 to 25°C | ≤ 85 °C | ≤ 125°C | Unit |
| f _{max} | Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 4) | 2.0 3.0 4.5 6.0 | 6.0 15 30 35 | 4.8 10 24 28 | 4.0 8.0 20 24 | MHz |
| t _{PLH} , t _{PHL} | Maximum Propagation Delay, Clock to Q or Q (Figures 1 and 4) | 2.0 3.0 4.5 6.0 | 100 75 20 17 | 125 90 25 21 | 150 120 30 26 | ns |
| t _{PLH} , t _{PHL} | Maximum Propagation Delay, Set or Reset to Q or \overline{Q} (Figures 2 and 4) | 2.0 3.0 4.5 6.0 | 105 80 21 18 | 130 95 26 22 | 160 130 32 27 | ns |
| t _{TLH} , t _{THL} | Maximum Output Transition Time, Any Output (Figures 1 and 4) | 2.0 3.0 4.5 6.0 | 75 30 15 13 | 95 40 19 16 | 110 55 22 19 | ns |
| C _{in} | Maximum Input Capacitance | _ | 10 | 10 | 10 | pF |

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

| | | Typical @ 25°C, V _{CC} = 5.0 V | |
|----------|--|---|----|
| C_{PD} | Power Dissipation Capacitance (Per Flip-Flop)* | 32 | pF |

^{*} Used to determine the no-load dynamic power consumption: $P_D = C_{PD} \, V_{CC}^2 f + I_{CC} \, V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS (Input $t_r = t_f = 6.0 \text{ ns}$)

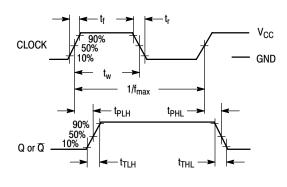
| | | | Gu | aranteed Li | mit | |
|---------------------------------|--|--------------------------|---------------------------|---------------------------|---------------------------|------|
| Symbol | Parameter | V _{CC} (V) | – 55 to 25°C | ≤ 85 °C | ≤ 125°C | Unit |
| t _{su} | Minimum Setup Time, Data to Clock (Figure 3) | 2.0 3.0 4.5 6.0 | 80 35 16 14 | 100 45 20 17 | 120 55 24 20 | ns |
| t _h | Minimum Hold Time, Clock to Data (Figure 3) | 2.0 3.0 4.5 6.0 | 3.0 3.0 3.0 3.0 | 3.0 3.0 3.0 3.0 | 3.0 3.0 3.0 3.0 | ns |
| t _{rec} | Minimum Recovery Time, Set or Reset Inactive to Clock (Figure 2) | 2.0 3.0 4.5 6.0 | 8.0 8.0 8.0 8.0 | 8.0 8.0 8.0 8.0 | 8.0 8.0 8.0 8.0 | ns |
| t _w | Minimum Pulse Width, Clock (Figure 1) | 2.0 3.0 4.5 6.0 | 60 25 12 10 | 75 30 15 13 | 90 40 18 15 | ns |
| t _w | Minimum Pulse Width, Set or Reset (Figure 2) | 2.0 3.0 4.5 6.0 | 60 25 12 10 | 75 30 15 13 | 90 40 18 15 | ns |
| t _r , t _f | Maximum Input Rise and Fall Times (Figures 1, 2, 3) | 2.0 3.0 4.5 6.0 | 1000 800 500 400 | 1000 800 500 400 | 1000 800 500 400 | ns |

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|-------------|----------------------|-----------------------|
| 74HC74D | SOIC-14 | |
| 74HC74DG | SOIC-14 (Pb-Free) | 55 Units / Rail |
| 74HC74DR2 | SOIC-14 | |
| 74HC74DR2G | SOIC-14 (Pb-Free) | 2500 / Tape & Reel |
| 74HC74DTR2 | TSSOP-14* | |
| 74HC74DTR2G | TSSOP-14* | |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb-Free.

SWITCHING WAVEFORMS



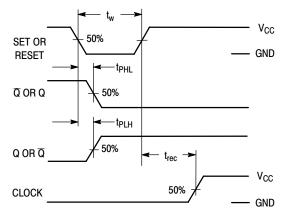
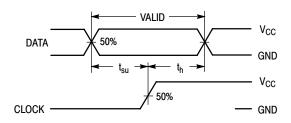
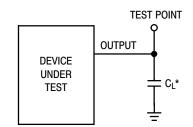


Figure 1.

Figure 2.







*Includes all probe and jig capacitance

Figure 4.

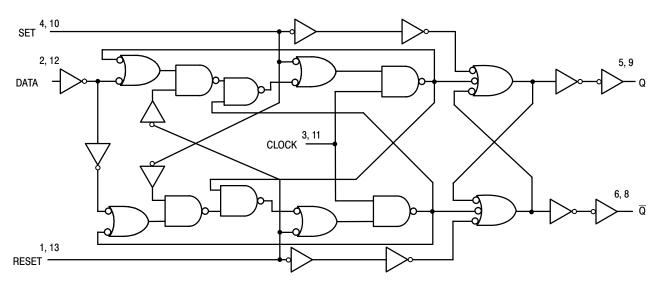
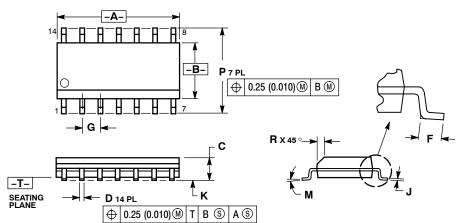


Figure 5. EXPANDED LOGIC DIAGRAM

PACKAGE DIMENSIONS

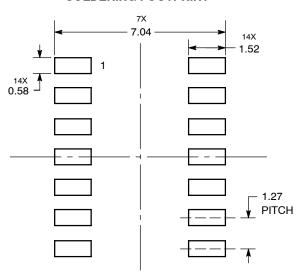
SOIC-14 CASE 751A-03 **ISSUE H**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

| | MILLIMETERS | | INC | HES |
|-----|-------------|------|-------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 8.55 | 8.75 | 0.337 | 0.344 |
| В | 3.80 | 4.00 | 0.150 | 0.157 |
| С | 1.35 | 1.75 | 0.054 | 0.068 |
| D | 0.35 | 0.49 | 0.014 | 0.019 |
| F | 0.40 | 1.25 | 0.016 | 0.049 |
| G | 1.27 | BSC | 0.050 | BSC |
| J | 0.19 | 0.25 | 0.008 | 0.009 |
| K | 0.10 | 0.25 | 0.004 | 0.009 |
| М | 0 ° | 7 ° | 0 ° | 7 ° |
| Р | 5.80 | 6.20 | 0.228 | 0.244 |
| R | 0.25 | 0.50 | 0.010 | 0.019 |

SOLDERING FOOTPRINT*

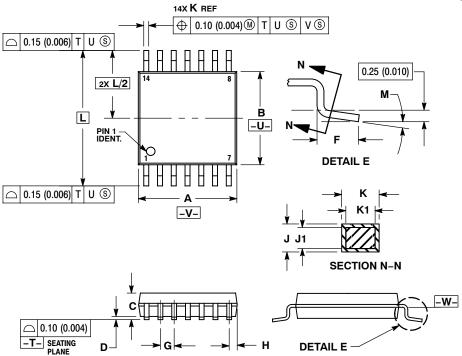


DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSSOP-14 CASE 948G-01 **ISSUE B**



NOTES:

- JIES:

 1. DIMENSIONING AND TOLERANCING PER
 ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD
 FLASH, PROTRUSIONS OR GATE BURRS.
 MOLD FLASH OR GATE BURRS SHALL NOT
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

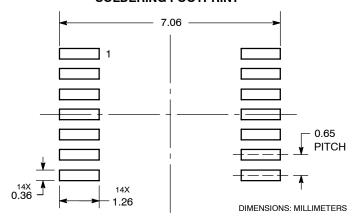
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMIIM MATERIAL DIMENSION AT MAXIMUM MATERIAL CONDITION.
- CONDITION.

 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

| | MILLIN | IETERS | INC | HES |
|-----|--------|--------|-----------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 4.90 | 5.10 | 0.193 | 0.200 |
| В | 4.30 | 4.50 | 0.169 | 0.177 |
| С | | 1.20 | | 0.047 |
| D | 0.05 | 0.15 | 0.002 | 0.006 |
| F | 0.50 | 0.75 | 0.020 | 0.030 |
| G | 0.65 | BSC | 0.026 | BSC |
| Н | 0.50 | 0.60 | 0.020 | 0.024 |
| J | 0.09 | 0.20 | 0.004 | 0.008 |
| J1 | 0.09 | 0.16 | 0.004 | 0.006 |
| K | 0.19 | 0.30 | 0.007 | 0.012 |
| K1 | 0.19 | 0.25 | 0.007 | 0.010 |
| L | 6.40 | BSC | 0.252 BSC | |
| М | 0 ° | 8 ° | 0 ° | 8 ° |

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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